

**Amendments to the Claims:**

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1-6. (Canceled).

7. (New) A method for producing a single crystal in accordance with Czochralski method by flowing an inert gas downward in a chamber of a single crystal-pulling apparatus and surrounding a single crystal pulled from a raw material melt with a gas flow-guide cylinder, wherein when a single crystal within N region outside OSF region generated in a ring shape in the radial direction of the single crystal is pulled, the single crystal within N region is pulled in a condition that flow amount of the inert gas between the single crystal and the gas flow-guide cylinder is 0.6 D(L/min) or more and pressure in the chamber is 0.6 D(hPa) or less, in which D (mm) is a diameter of the single crystal to be pulled.

8. (New) The method for producing a single crystal according to Claim 7, wherein the single crystal to be pulled is a silicon single crystal.

9. (New) The method for producing a single crystal according to Claim 7, wherein the diameter of the single crystal to be pulled is 200 mm or more.

10. (New) The method for producing a single crystal according to Claim 8, wherein the diameter of the single crystal to be pulled is 200 mm or more.

11. (New) The method for producing a single crystal according to Claim 7, wherein the single crystal within N region is pulled by using the gas flow-guide cylinder that Fe concentration is 0.05 ppm or less, at least, in a surface thereof.

12. (New) The method for producing a single crystal according to Claim 8, wherein the single crystal within N region is pulled by using the gas flow-guide cylinder that Fe concentration is 0.05 ppm or less, at least, in a surface thereof.

13. (New) The method for producing a single crystal according to Claim 9, wherein the single crystal within N region is pulled by using the gas flow-guide cylinder that Fe concentration is 0.05 ppm or less, at least, in a surface thereof.

14. (New) The method for producing a single crystal according to Claim 10, wherein the single crystal within N region is pulled by using the gas flow-guide cylinder that Fe concentration is 0.05 ppm or less, at least, in a surface thereof.

15. (New) A single crystal produced by the method according to Claim 7.

16. (New) A single crystal produced by the method according to Claim 8.

17. (New) A single crystal produced by the method according to Claim 9.

18. (New) A single crystal produced by the method according to Claim 10.

19. (New) A single crystal produced by the method according to Claim 11.

20. (New) A single crystal produced by the method according to Claim 12.

21. (New) A single crystal produced by the method according to Claim 13.

22. (New) A single crystal produced by the method according to Claim 14.

23. (New) A silicon single crystal wafer having a diameter of 200 mm or more produced in accordance with Czochralski method, wherein the wafer is occupied by N region outside OSF region generated in a ring shape in the radial direction of a single crystal, and Fe concentration of the entire plane in the radial direction including a peripheral part of the wafer is  $1 \times 10^{10}$  atoms/cm<sup>3</sup> or less.